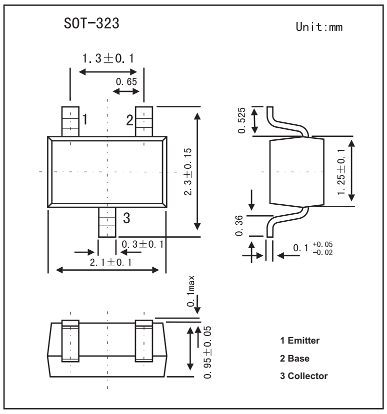
NPN Epitaxial Planar Silicon Transistor

2SC4555



■ Features

- ● Very small-sized package
- ● Low collector-to-emitter saturation voltage.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	500	mA
Collector current(Pulse)	I_{CP}	1	A
Collector dissipation	P_C	150	mW
Junction temperature	T_j	105	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 15V, I_E=0			0.1	µA
Emitter cutoff current	I_{EBO}	V_{EB} = 4V, I_C=0			0.1	µA
DC current gain	h_{FE}	V_{CE} = 2V , I_C = 10mA	135		600	
Gain bandwidth product	f_T	V_{CE} = 2V , I_C = 50mA		300		MHz
Output capacitance	C_{ob}	V_{CB} = 10V, f = 1MHz		4.0		pF
Collector-to-emitter saturation voltage	$V_{CE(sat)}$	I_C = 5mA , I_B = 0.5mA			30	V
		I_C = 200mA , I_B = 10mA		160	300	
Base-to-emitter saturation voltage	$V_{BE(sat)}$	I_C = 200mA , I_B = 10mA		0.95	1.2	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10µA , I_E = 0	20			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	15			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10µA , I_C = 0	5			V

■ h_{FE} Classification

Marking	UT		
Rank	5	6	7
hFE	135～270	200～400	300～600